



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

re the Application of

MAEDA et al

Serial No.: 09/808,016

Filed: March 15, 2001

For: FILM-FORMING SURFACE
REFORMING METHOD AND
SEMICONDUCTOR DEVICE
MANUFACTURING METHOD

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) Art Unit: 2829
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) Examiner: Kilday
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AMENDMENT ACCOMPANYING RCE

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Please rewrite claims 8, 16 and 23 as follows:

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8. (Twice Amended) A semiconductor device manufacturing method comprising the steps of:

(a) contacting a surface of a silicon oxide film with an aqueous solution containing any

C1 one of NO₂ and NO₃; and

(b) forming an insulating film by CVD on the surface as obtained in step (a) after the

film-forming surface is contacted with the aqueous solution.

16. (Amended) A semiconductor device manufacturing method comprising the steps of:

C2 (a) bringing a gas or an aqueous solution containing an etchant selected from the group